**Product data sheet** 

# 1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

## 2. Features and benefits

- Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- · Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

## 3. Applications

· Output rectifiers in high-frequency switched-mode power supplies

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Val	lues		Unit
		Conditions		Val	1403		Offic
	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		150				V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2	8			А	
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 128 °C; square-wave pulse	16			А	
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	80			Α	
forward current		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	88		Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics			,			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	- 0.92 1.05		1.05	V	
Dynamic	characteristics			,			
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; ramp recovery; Fig. 5; Fig. 7$		-	20	25	ns
Electrost	atic discharge						
$V_{ESD}$	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode		K — A 001aaa020
mb	mb	mounting base; cathode	1 2 TO-220AC (SOD59)	001aaa020

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BYW29E-150	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

# 7. Marking

## **Table 4. Marking codes**

Type number	Marking codes
BYW29E-150	BYW29E-150

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		150	V
$V_{RWM}$	crest working reverse voltage		150	V
$V_R$	reverse voltage		150	V
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5 ; $T_{mb} \le$ 128 °C ;square-wave pulse; Fig. 1; Fig. 2	8	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 128 °C; square-wave pulse	16	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	80	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	88	А
I <sub>RRM</sub>	repetitive peak reverse current	$\delta = 0.001 \; ; t_p = 2 \; \mu s$	0.2	А
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	0.2	А
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C
Electrosta	atic discharge		-	1
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ	8	kV

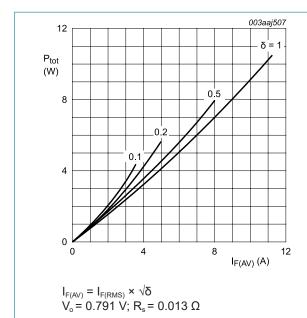
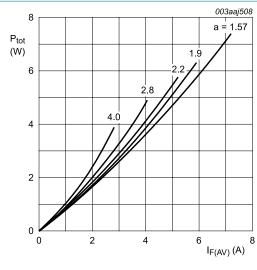


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$ V<sub>o</sub> = 0.791 V; R<sub>s</sub> = 0.013  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

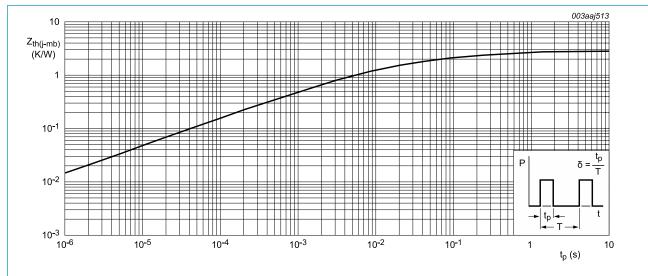
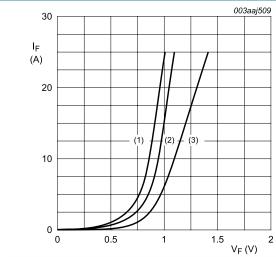


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse width

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	0.92	1.05	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 150 V; T <sub>j</sub> = 25 °C	-	2	10	μA
		V <sub>R</sub> = 150 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic	characteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 5; Fig. 6$	-	4	11	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A}/\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; ramp recovery; Fig. 5; Fig. 7	-	20	25	ns
		$I_F = 0.5 \text{ A}$ ; $I_R = 1 \text{ A}$ ; $I_{R(meas)} = 0.25 \text{ A}$ ; $I_{j} = 25 \text{ °C}$ ; step recovery; Fig. 8	-	15	20	ns
V <sub>FRM</sub>	forward recovery voltage	$I_F = 1 \text{ A}$ ; $dI_F/dt = 10 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 9	-	1	-	V





<sup>(2)</sup> T<sub>i</sub> = 150 °C; maximum values

 $V_o = 0.791 \text{ V}; R_s = 0.013 \Omega$ Fig. 4. Forward current as a function of forward voltage



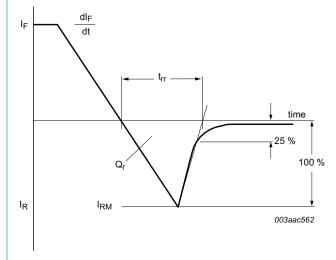
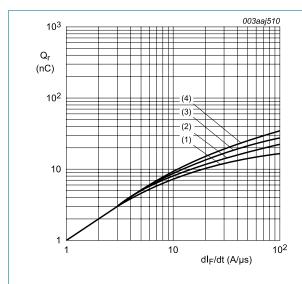


Fig. 5. Reverse recovery definitions; ramp recovery

<sup>(3)</sup>  $T_j = 25$  °C; maximum values



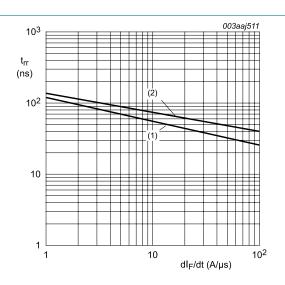
(1) 
$$I_F = 1 A$$
;  $T_j = 25 °C$ 

(2) 
$$I_F = 2 A$$
;  $T_i = 25 °C$ 

(3) 
$$I_F = 5 A$$
;  $T_j = 25 °C$ 

(4) 
$$I_F = 10 \text{ A}$$
;  $T_j = 25 \text{ °C}$ 

Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values



(1) 
$$I_F = 1 \text{ A}$$
;  $T_j = 25 ^{\circ}\text{C}$   
(2)  $I_F = 10 \text{ A}$ ;  $T_i = 25 ^{\circ}\text{C}$ 

Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

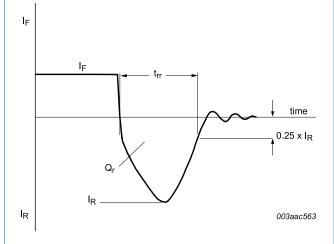


Fig. 8. Reverse recovery definitions; step recovery

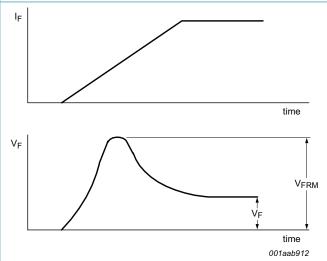
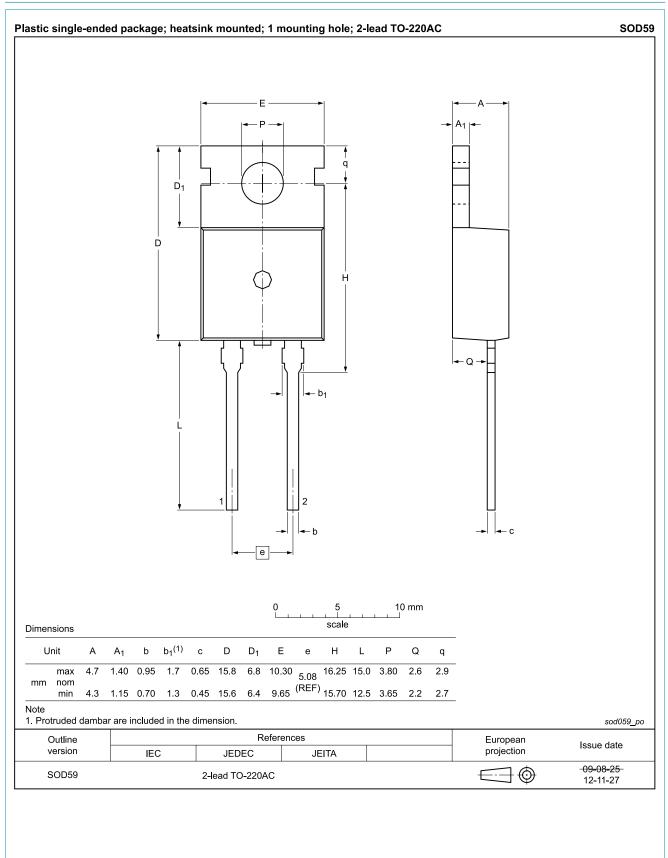


Fig. 9. Forward recovery definitions

# 11. Package outline



## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Ultrafast power diode

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Date of release: 4 June 2018

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